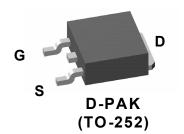
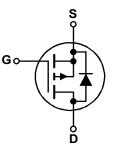
FAIRCHILD FDD4685 40V P-Channel PowerTrench <sup>0</sup> -40V, -32A, 27mΩ	® MOSFET
Features	General Description
■ Max $r_{DS(on)}$ = 27m $\Omega$ at V <sub>GS</sub> = -10V, I <sub>D</sub> = -8.4A	This P-Channel MOSFET has been produced using Fairchild
■ Max $r_{DS(on)}$ = 35m $\Omega$ at $V_{GS}$ = -4.5V, $I_D$ = -7A	Semiconductor's proprietary PowerTrench <sup>®</sup> technology to deliver low $r_{DS(on)}$ and good switching characteristic offering
High performance trench technology for extremely low r <sub>DS(on)</sub>	superior performance in application.
■ RoHS Compliant	



## Application

- Inverter
- Power Supplies





## MOSFET Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter			Parameter Ratings	
V <sub>DS</sub>	Drain to Source Voltage			-40	V
V <sub>GS</sub>	Gate to Source Voltage			±20	V
	Drain Current -Continuous(Package Limited)	T <sub>C</sub> = 25°C		-32	
I <sub>D</sub>	-Continuous(Silicon Limited)	T <sub>C</sub> = 25°C	(Note 1)	-40	
	-Continuous	T <sub>A</sub> = 25°C	(Note 1a)	-8.4	Α
	-Pulsed			-100	
E <sub>AS</sub>	Drain-Source Avalanche Energy		(Note 3)	121	mJ
D	Power Dissipation $T_c = 25^{\circ}C$		69	w	
PD			3	vv	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range			–55 to +150	°C

## **Thermal Characteristics**

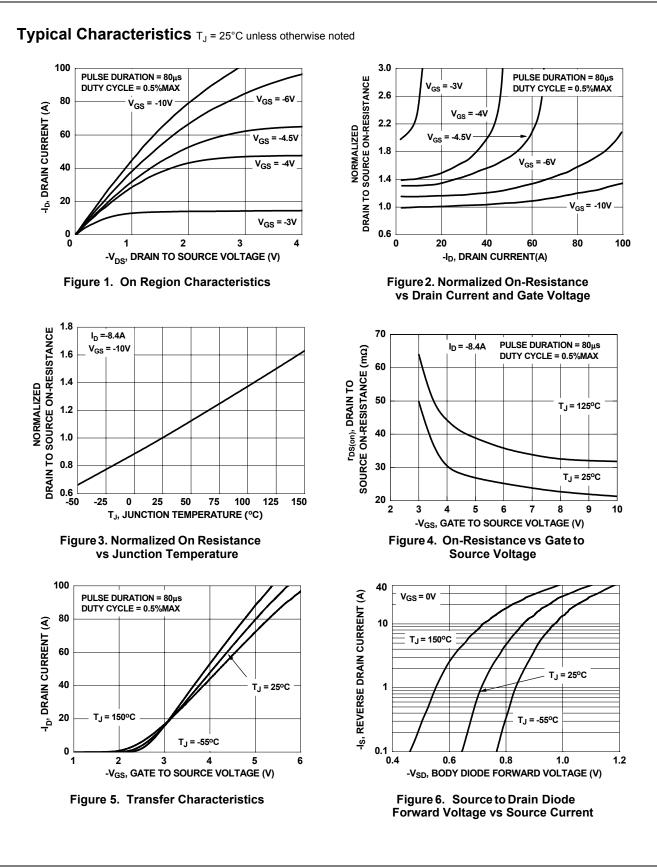
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction to Case	1.8	°C/W
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction to Ambient (Note 1	a) 40	0/00

### **Package Marking and Ordering Information**

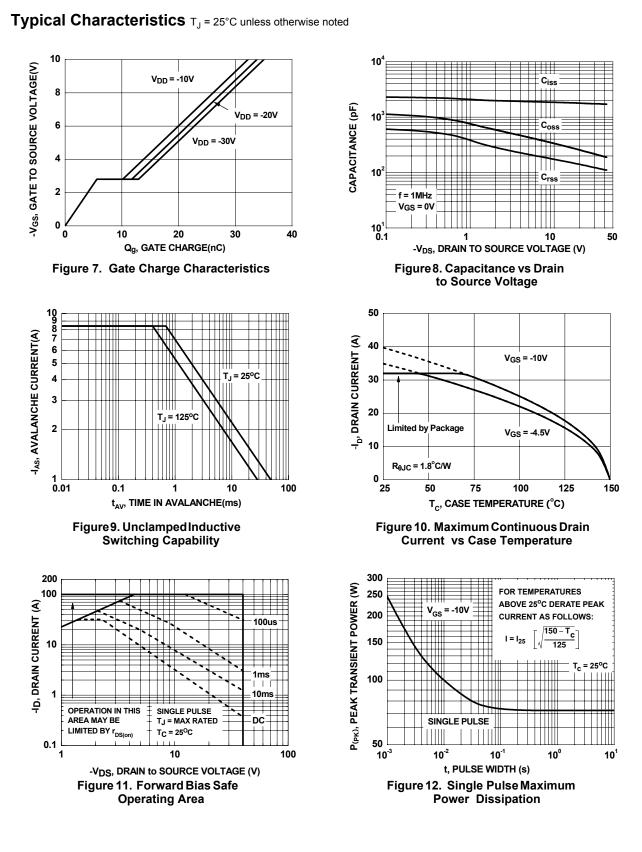
Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDD4685	FDD4685	D-PAK(TO-252)	13"	16mm	2500 units

Cteristics         Drain to Source Breakdown Voltage         Breakdown Voltage Temperature         Coefficient         Zero Gate Voltage Drain Current         Gate to Source Leakage Current         Cteristics (Note 2)         Gate to Source Threshold Voltage	$I_{D} = -250\mu A, V_{GS} = 0V$ $I_{D} = -250\mu A, referenced to 25°C$ $V_{DS} = -32V, V_{GS} = 0V$ $V_{GS} = \pm 20V, V_{GS} = 0V$	-40	<b>Typ</b>		V
Drain to Source Breakdown Voltage Breakdown Voltage Temperature Coefficient Zero Gate Voltage Drain Current Gate to Source Leakage Current Cteristics (Note 2)	$I_D = -250 \mu A$ , referenced to 25°C $V_{DS} = -32V$ , $V_{GS} = 0V$	-40	-33		V
Breakdown Voltage Temperature Coefficient Zero Gate Voltage Drain Current Gate to Source Leakage Current Cteristics (Note 2)	$I_D = -250 \mu A$ , referenced to 25°C $V_{DS} = -32V$ , $V_{GS} = 0V$		-33		
Gate to Source Leakage Current cteristics (Note 2)					mV/°C
cteristics (Note 2)				-1	μA
				±100	nA
	$V_{GS} = V_{DS}, I_{D} = -250 \mu A$	-1	-1.6	-3	V
Gate to Source Threshold Voltage		-1		-5	
Temperature Coefficient	$I_D = -250\mu A$ , referenced to $25^{\circ}C$		4.9		mV/°C
	$V_{GS} = -10V, I_D = -8.4A$		23	27	
Static Drain to Source On Resistance	$V_{GS} = -4.5V, I_D = -7A$		30	35	mΩ
	$V_{GS}$ = -10V, $I_{D}$ = -8.4A, $T_{J}$ =125°C		33	42	
Forward Transconductance	$V_{DS} = -5V, I_{D} = -8.4A$		23		S
Characteristics					
1			1790	2380	pF
	$V_{\rm DS} = -20V, V_{\rm GS} = 0V,$				pF
	f = 1MHz		140		pF
Gate Resistance	f = 1MHz		4		Ω
Characteristics					
			- 1		
Turn-On Delay Time	$V_{DD} = -20V I_D = -8.4A$		8	16	ns
Rise Time	$-V_{DD} = -20V, I_D = -8.4A$ $-V_{GS} = -10V, R_{GEN} = 6\Omega$		15	27	ns
Rise Time Turn-Off Delay Time	$V_{DD} = -20V, I_D = -8.4A$ $V_{GS} = -10V, R_{GEN} = 6\Omega$		15 34	27 55	ns ns
Rise Time Turn-Off Delay Time Fall Time	$-V_{GS} = -10V, R_{GEN} = 6\Omega$		15 34 14	27 55 26	ns ns ns
Rise Time Turn-Off Delay Time Fall Time Total Gate Charge	$V_{GS} = -10V, R_{GEN} = 6\Omega$		15 34 14 19	27 55	ns ns ns nC
Rise Time Turn-Off Delay Time Fall Time Total Gate Charge Gate to Source Gate Charge	$-V_{GS} = -10V, R_{GEN} = 6\Omega$		15 34 14 19 5.6	27 55 26	ns ns nC nC
Rise Time Turn-Off Delay Time Fall Time Total Gate Charge	$V_{GS} = -10V, R_{GEN} = 6\Omega$		15 34 14 19	27 55 26	ns ns ns nC
Rise Time Turn-Off Delay Time Fall Time Total Gate Charge Gate to Source Gate Charge	$V_{GS} = -10V, R_{GEN} = 6\Omega$		15 34 14 19 5.6	27 55 26	ns ns nC nC
Rise Time Turn-Off Delay Time Fall Time Total Gate Charge Gate to Source Gate Charge Gate to Drain "Miller" Charge	$V_{GS} = -10V, R_{GEN} = 6\Omega$		15 34 14 19 5.6	27 55 26	ns ns nC nC
Rise Time Turn-Off Delay Time Fall Time Total Gate Charge Gate to Source Gate Charge Gate to Drain "Miller" Charge rce Diode Characteristics	$V_{GS} = -10V, R_{GEN} = 6\Omega$ $V_{DD} = -20V, I_D = -8.4A$ $V_{GS} = -5V$		15 34 14 19 5.6 6.1	27 55 26 27	ns ns nC nC nC
	Forward Transconductance Characteristics Input Capacitance Output Capacitance Reverse Transfer Capacitance Gate Resistance	Static Drain to Source On Resistance $V_{GS} = -4.5V$ , $I_D = -7A$ $V_{GS} = -10V$ , $I_D = -8.4A$ , $T_J = 125^{\circ}C$ Forward Transconductance $V_{DS} = -5V$ , $I_D = -8.4A$ CharacteristicsInput Capacitance $V_{DS} = -20V$ , $V_{GS} = 0V$ ,Output Capacitance $f = 1MHz$ Gate Resistance $f = 1MHz$	Static Drain to Source On Resistance $V_{GS} = -4.5V$ , $I_D = -7A$ $V_{GS} = -10V$ , $I_D = -8.4A$ , $T_J = 125^{\circ}C$ Forward Transconductance $V_{DS} = -5V$ , $I_D = -8.4A$ CharacteristicsInput Capacitance $V_{DS} = -20V$ , $V_{GS} = 0V$ ,Output Capacitance $f = 1MHz$ Gate Resistance $f = 1MHz$	Static Drain to Source On Resistance $V_{GS} = -4.5V$ , $I_D = -7A$ 30 $V_{GS} = -10V$ , $I_D = -8.4A$ , $T_J = 125^{\circ}C$ 33Forward Transconductance $V_{DS} = -5V$ , $I_D = -8.4A$ 23CharacteristicsInput Capacitance $V_{DS} = -20V$ , $V_{GS} = 0V$ , f = 1MHz1790Output Capacitance $V_{DS} = -20V$ , $V_{GS} = 0V$ , f = 1MHz140	Static Drain to Source On Resistance $V_{GS} = -4.5V$ , $I_D = -7A$ 30       35 $V_{GS} = -10V$ , $I_D = -8.4A$ , $T_J = 125^{\circ}C$ 33       42         Forward Transconductance $V_{DS} = -5V$ , $I_D = -8.4A$ 23         Characteristics         Input Capacitance $V_{DS} = -20V$ , $V_{GS} = 0V$ , f = 1MHz       1790       2380         Qutput Capacitance $V_{DS} = -20V$ , $V_{GS} = 0V$ , f = 1MHz       140       205

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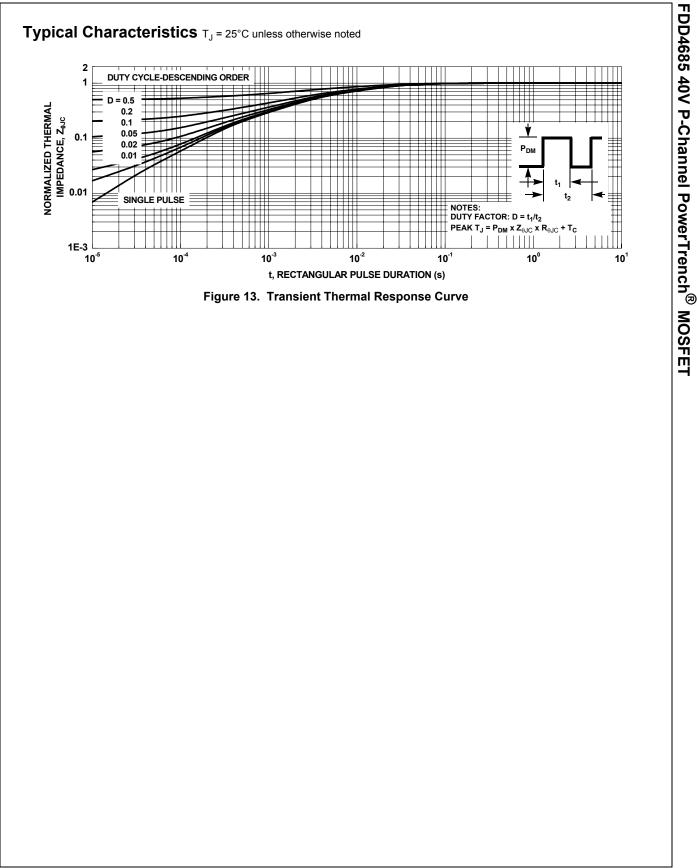


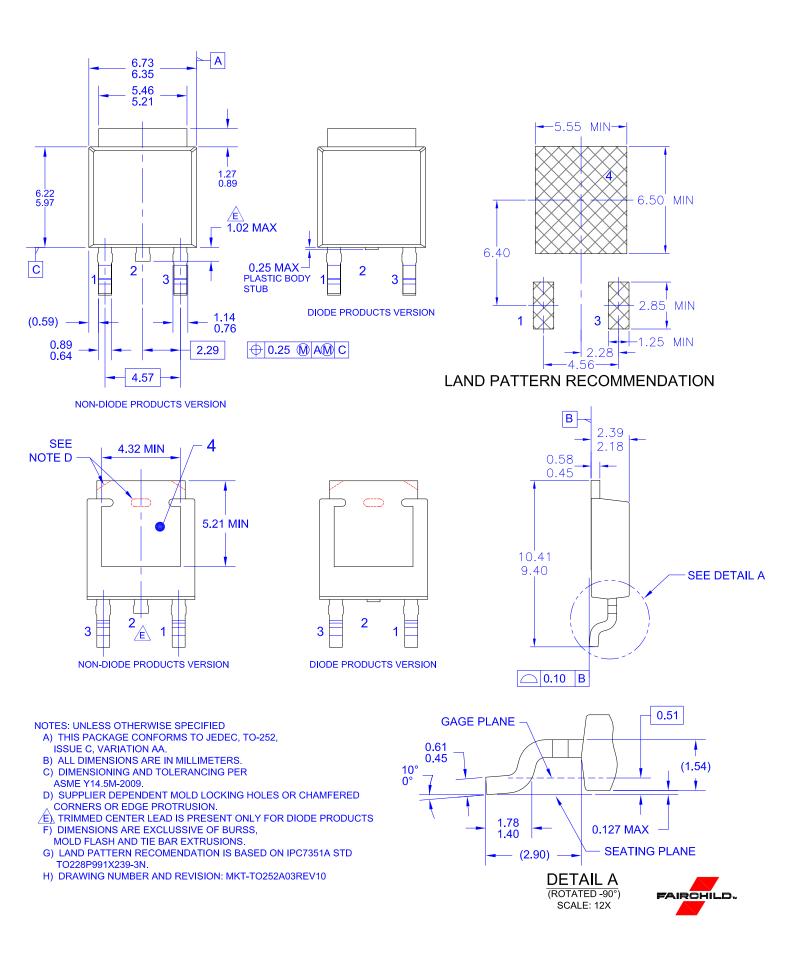
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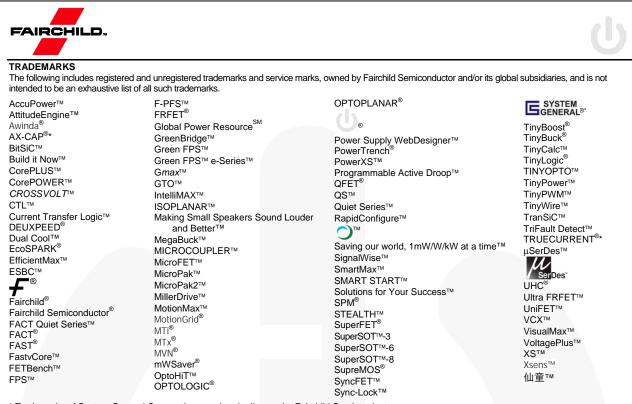


FDD4685 40V P-Channel PowerTrench<sup>®</sup> MOSFET

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